

A simulation study of temperature of partially shaded modules

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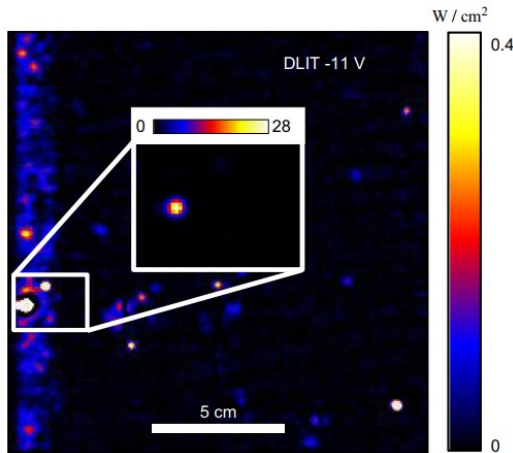
Motivation

- Hot spots: most important degradation mode*
- Larger module, higher power
- Residential application

Industry progress of solar cells

- In the past:

p-type multicrystalline Si solar cell



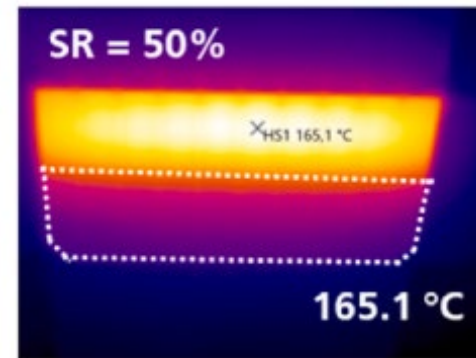
dark lock-in thermography image
reverse biased at -11V

I. Geysmeyer et al., Solar energy materials & solar cells (120), 2014

→ Global reverse IV curve is not sufficient to predict temperature

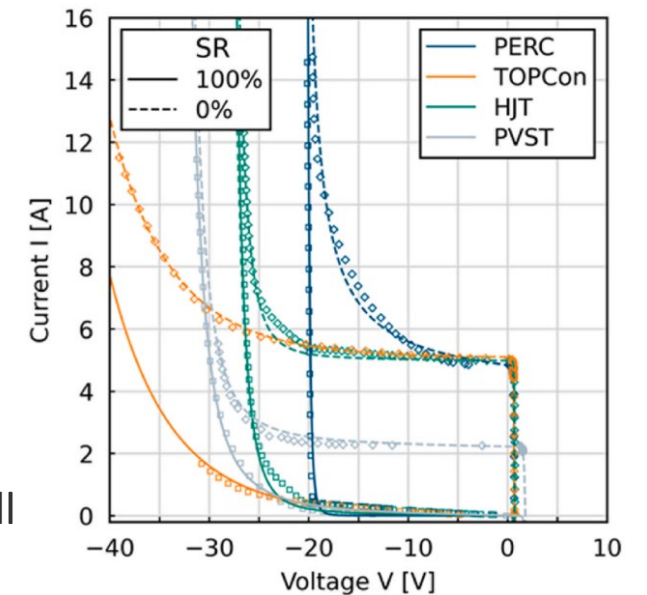
- Recent years:

uniform breakdown

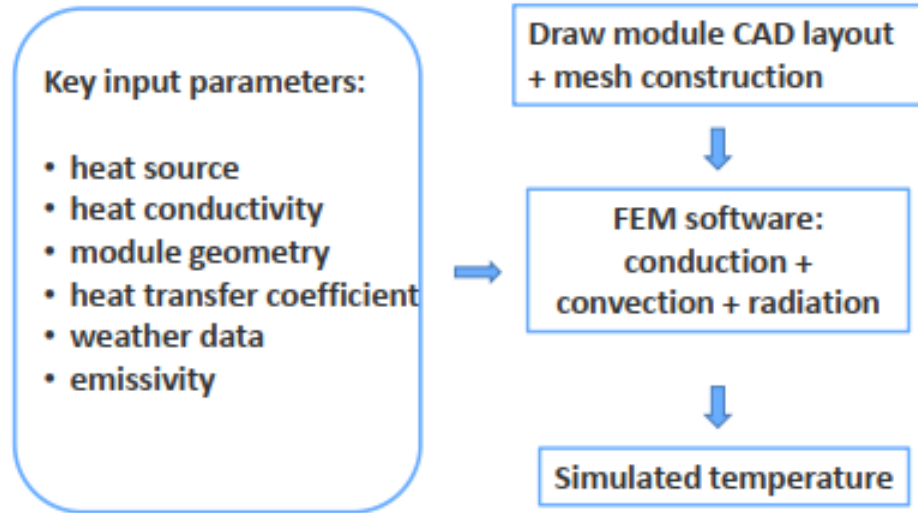


IR image of a shaded PERC cell

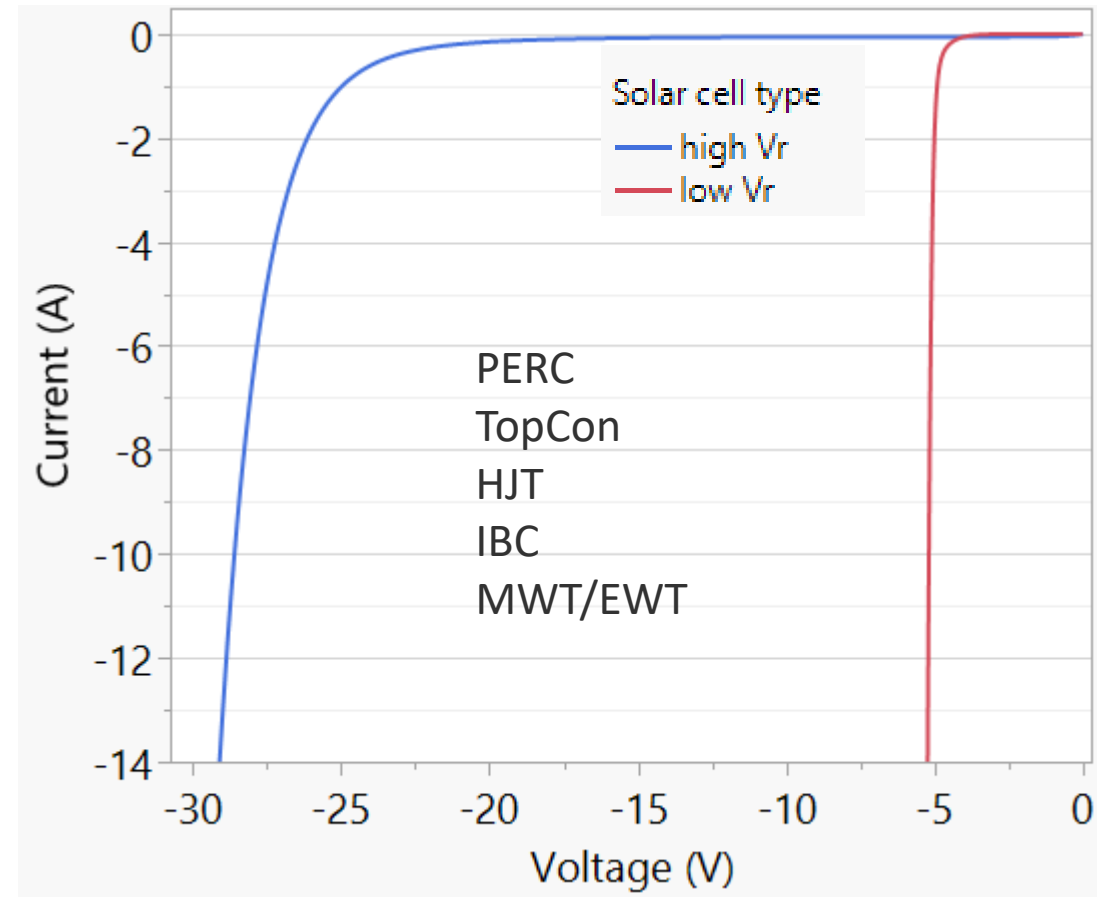
C. Reichel et al., Solar energy materials & solar cells (276), 2024



Simulation



- Our simulation involves many assumptions and approximations.
- Simulate a solar cell with a breakdown voltage V_r of -5V and -20V

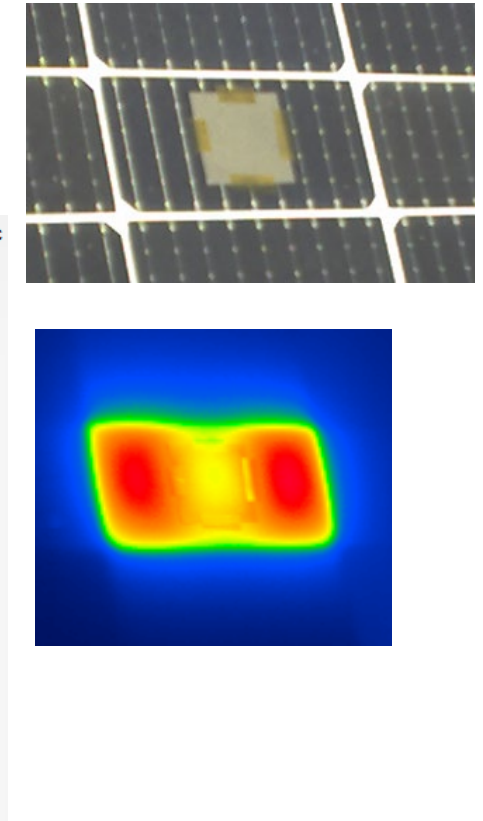
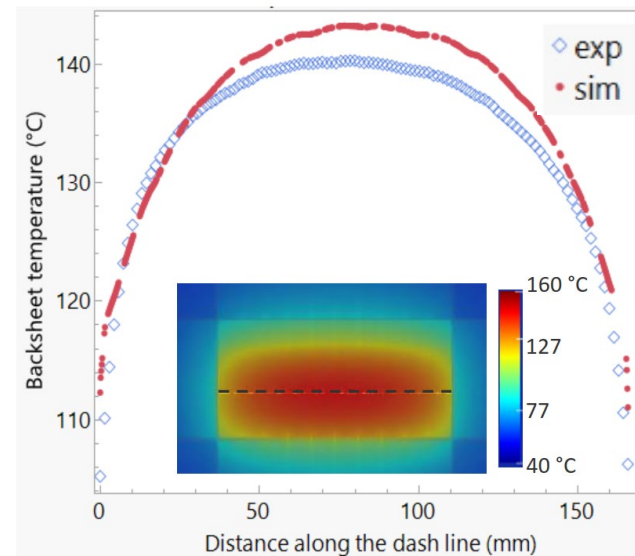
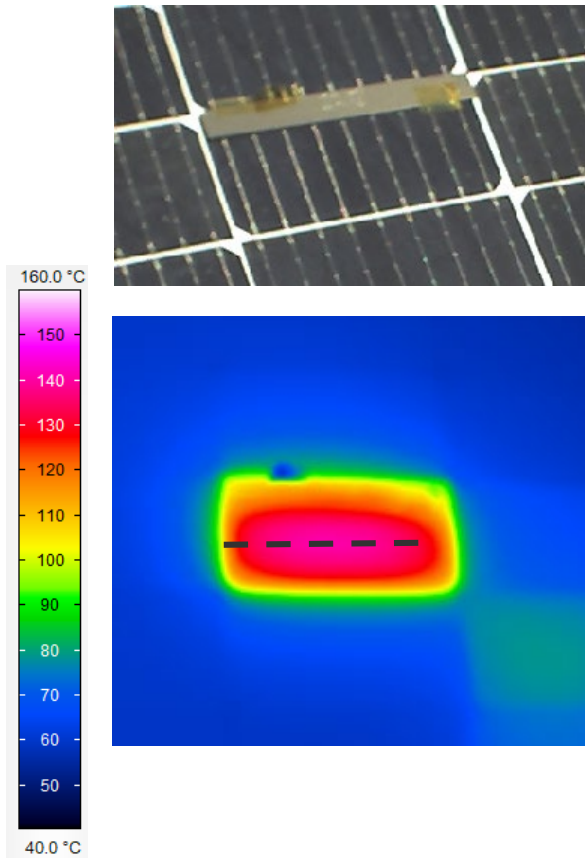


Exp. vs Sim.

120 half-cell PERC module (M6 wafers)

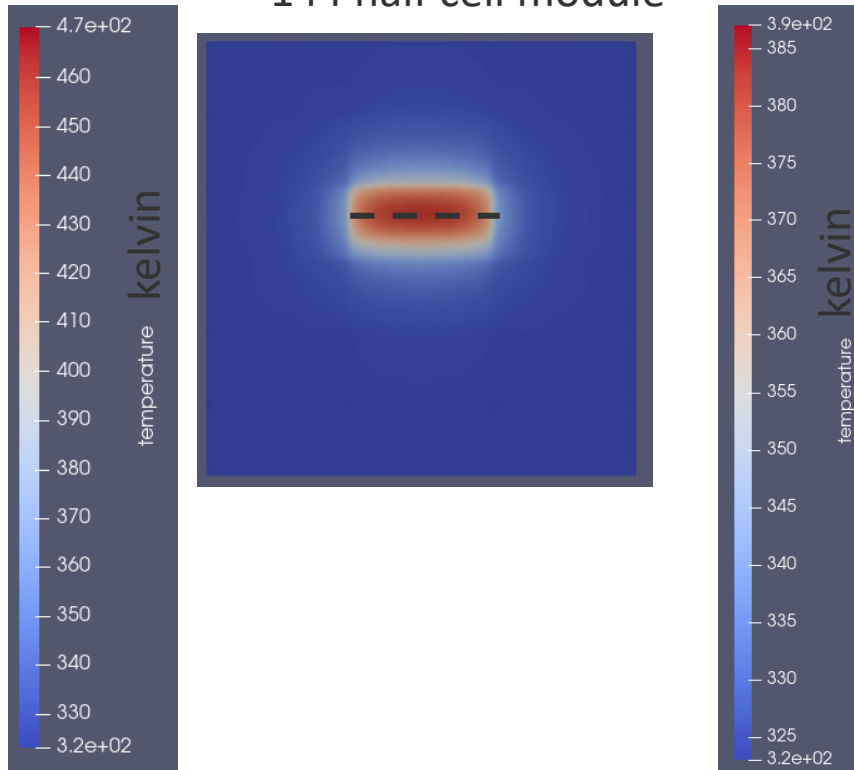
- Shading shape A*
22.5% of a half cell is shaded

- Shading shape B
same cell measured on a different date
22.5% of a half cell is shaded

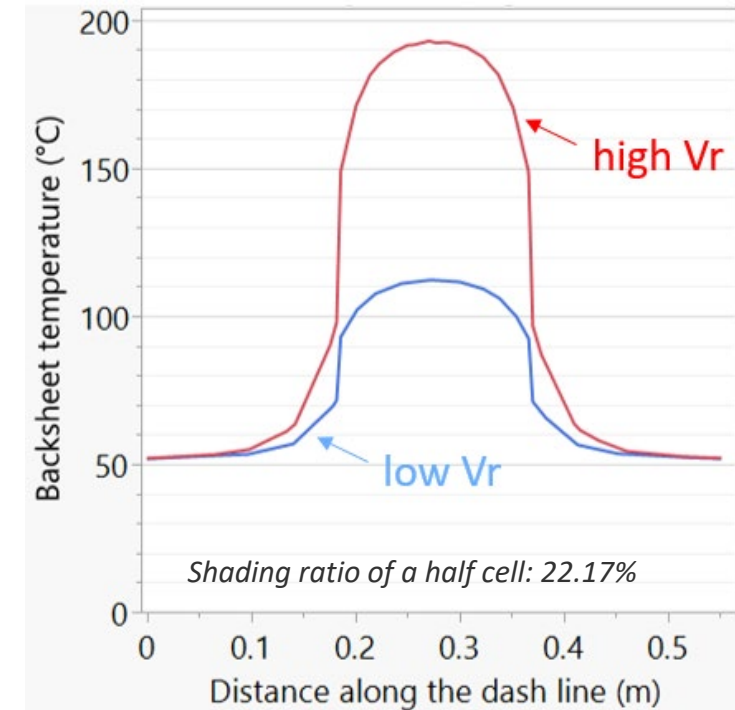
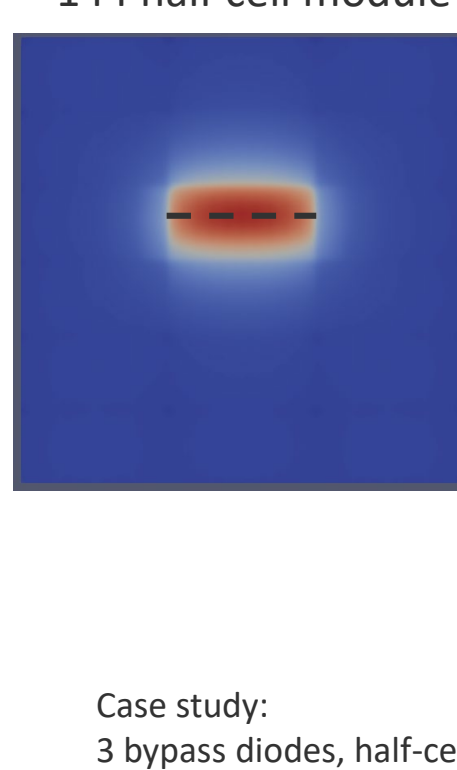


Simulation results: high and low Vr

Cells with high Vr
144 half cell module



Cells with low Vr
144 half cell module



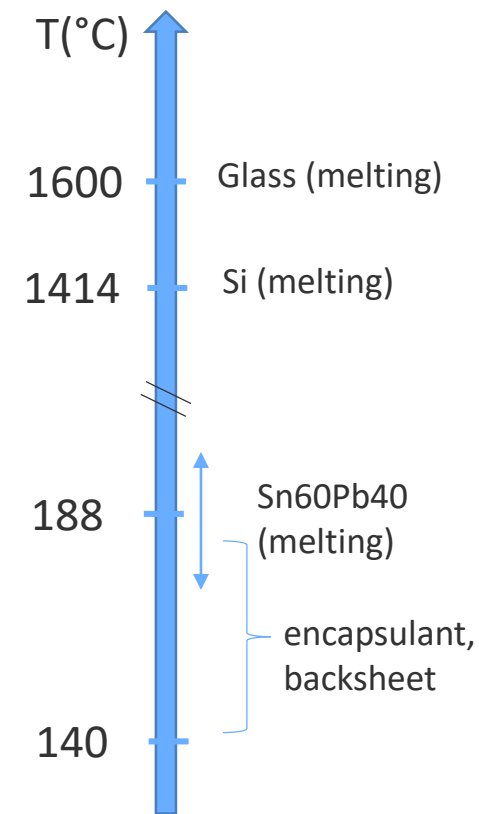
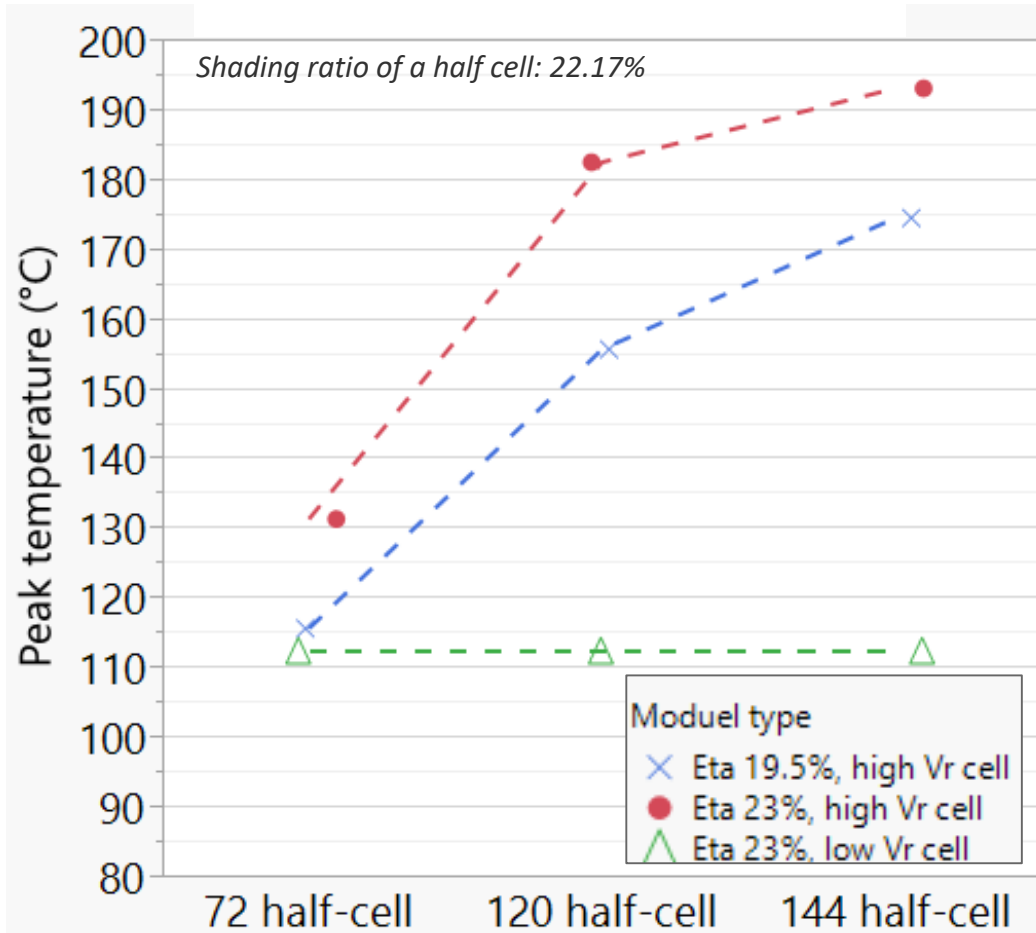
Case study:

3 bypass diodes, half-cell module, Module Eta 23%, M10 wafers

Tair =30 °C, wind speed = 10km/h, One sun illumination

Worst case (current of shaded module = current of unshaded module)

Simulation results: high and low Vr



Temperature coefficient: 0.38%/°C, 0.29%/°C



Step 2: Challenges (hard to be studied by simulation)

- 60×10^9 c-Si cells / 1×10^9 modules \rightarrow 500GW annual capacity

Simulation study is based on ideal situation (uniform heating under reverse bias condition)

Variations of cell's and module's processes in mass production

Not clear:

- Influence of reverse bias on solar cell efficiency and influence of long-term reverse bias*
- Hot-spot + Factor "X" (cracks, PID, T and H, solder joints failure) **

* E. Özkalay et al., *EPJ Photovolt.*, 15 (2024) 7

**M. Dhimish and A. Tyrrell, *npj Materials Degradation* (2022) 6,11

M. Afridi et al., *Solar Energy* (2023) 249, 467-475

Step 2: Challenges (hard to be studied by simulation)

- Many ways to mitigate this problem:
 - less cell per bypass diode
 - design of breakdown voltage
 - use an inverter that chooses local Pmpp at high-voltage *

- To be bulletproof: regular inspection/maintenance

- Awareness from the general public

* E. Bende et al., EUPVSEC 2014, p2546, Amsterdam, the Netherlands

Summary

- Ideal uniform breakdown can still show high temperature
- High V_r : T_{peak} increases with power of the substring
- Low V_r : T_{peak} depends on reverse I/V curve
- Difficult to simulate some factors on the field

